

## CoolMOS™ Power Transistor

### Features

- New revolutionary high voltage technology
- Extreme dv/dt rated
- High peak current capability
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Pb-free lead plating; RoHS compliant
- Ultra low gate charge
- Ultra low effective capacitances

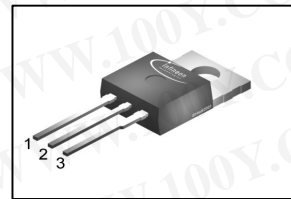
### CoolMOS™ 800V designed for:

- Industrial application with high DC bulk voltage
- Switching Application (i.e. active clamp forward)

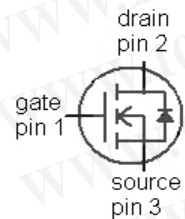
### Product Summary

$V_{DS}$	800	V
$R_{DS(on)max} @ T_j = 25^\circ C$	0.45	$\Omega$
$Q_{g,typ}$	64	nC

PG-TO220-3



Type	Package	Marking
SPP11N80C3	PG-TO220-3	11N80C3



### Maximum ratings, at $T_j=25^\circ C$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	$I_D$	$T_C=25^\circ C$	11	A
		$T_C=100^\circ C$	7.1	
Pulsed drain current <sup>2)</sup>	$I_{D,pulse}$	$T_C=25^\circ C$	33	
Avalanche energy, single pulse	$E_{AS}$	$I_D=2.2 A, V_{DD}=50 V$	470	mJ
Avalanche energy, repetitive $t_{AR}^{2),3)}$	$E_{AR}$	$I_D=11 A, V_{DD}=50 V$	0.2	
Avalanche current, repetitive $t_{AR}^{2),3)}$	$I_{AR}$		11	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0...640 V$	50	V/ns
Gate source voltage	$V_{GS}$	static	$\pm 20$	V
		AC ( $f > 1 Hz$ )	$\pm 30$	
Power dissipation	$P_{tot}$	$T_C=25^\circ C$	156	W
Operating and storage temperature	$T_j, T_{stg}$		-55 ... 150	$^\circ C$
Mounting torque		M3 and M3.5 screws	60	Ncm

Maximum ratings, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	$I_S$	$T_C=25\text{ }^\circ\text{C}$	11	A
Diode pulse current <sup>2)</sup>	$I_{S,pulse}$		33	
Reverse diode $dv/dt$ <sup>4)</sup>	$dv/dt$		4	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

#### Thermal characteristics

Thermal resistance, junction - case	$R_{thJC}$		-	-	0.8	K/W
Thermal resistance, junction - ambient	$R_{thJA}$	leaded	-	-	62	
Soldering temperature, wave soldering only allowed at leads	$T_{sold}$	1.6 mm (0.063 in.) from case for 10s	-	-	260	$^\circ\text{C}$

Electrical characteristics, at  $T_j=25\text{ }^\circ\text{C}$ , unless otherwise specified

#### Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=250\text{ }\mu\text{A}$	800	-	-	V
Avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0\text{ V}, I_D=11\text{ A}$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=0.68\text{ mA}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=800\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ }^\circ\text{C}$	-	-	20	$\mu\text{A}$
		$V_{DS}=800\text{ V}, V_{GS}=0\text{ V}, T_j=150\text{ }^\circ\text{C}$	-	100	-	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=7.1\text{ A}, T_j=25\text{ }^\circ\text{C}$	-	0.39	0.45	$\Omega$
		$V_{GS}=10\text{ V}, I_D=7.1\text{ A}, T_j=150\text{ }^\circ\text{C}$	-	1.05	-	
Gate resistance	$R_G$	$f=1\text{ MHz}, \text{open drain}$	-	1.2	-	$\Omega$

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic characteristics**

Input capacitance	$C_{iss}$	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	1600	-	pF
Output capacitance	$C_{oss}$		-	65	-	
Effective output capacitance, energy related <sup>5)</sup>	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 480 V	-	50	-	
Effective output capacitance, time related <sup>6)</sup>	$C_{o(tr)}$		-	140	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=0/10\text{ V}, I_D=11\text{ A},$ $R_G=7.5\text{ }\Omega, T_j=25\text{ }^\circ\text{C}$	-	25	-	ns
Rise time	$t_r$		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	72	-	
Fall time	$t_f$		-	10	-	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD}=640\text{ V}, I_D=11\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	8	-	nC
Gate to drain charge	$Q_{gd}$		-	30	-	
Gate charge total	$Q_g$		-	64	85	
Gate plateau voltage	$V_{plateau}$		-	5.5	-	V

**Reverse Diode**

Diode forward voltage	$V_{SD}$	$V_{GS}=0\text{ V}, I_F=I_S=11\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=400\text{ V},$ $I_F=I_S=11\text{ A},$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	550	-	ns
Reverse recovery charge	$Q_{rr}$		-	10	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	33	-	A

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> Pulse width  $t_p$  limited by  $T_{j,max}$

<sup>3)</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV}=E_{AR} \cdot f$ .

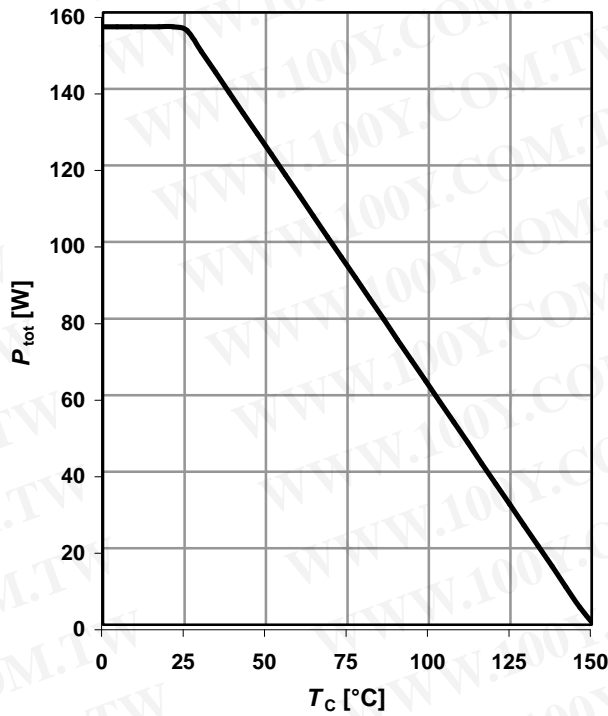
<sup>4)</sup>  $I_{SD}=I_D, di/dt=200\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak}<V_{(BR)DSS}, T_j<T_{j,max}$ , identical low side and high side switch

<sup>5)</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

<sup>6)</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

### 1 Power dissipation

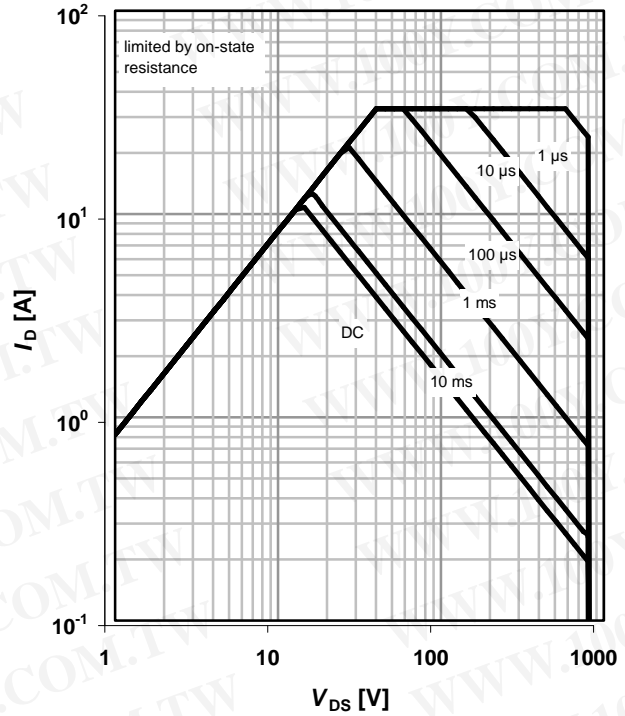
$$P_{tot} = f(T_C)$$



### 2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

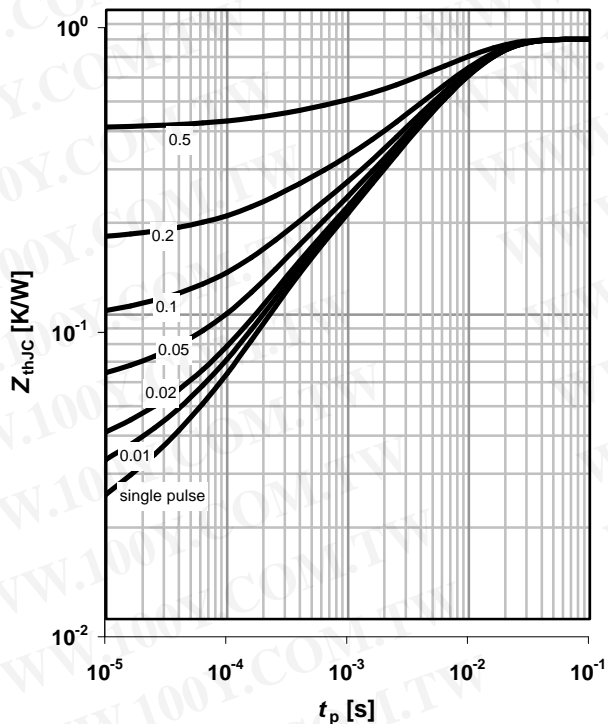
parameter:  $t_p$



### 3 Max. transient thermal impedance

$$Z_{thJC} = f(t_p)$$

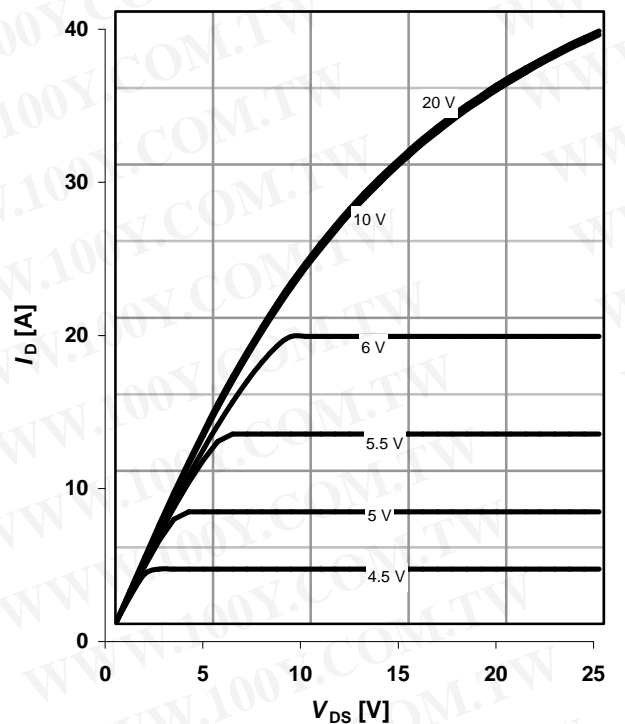
parameter:  $D = t_p / T$



### 4 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}; t_p = 10 \mu\text{s}$$

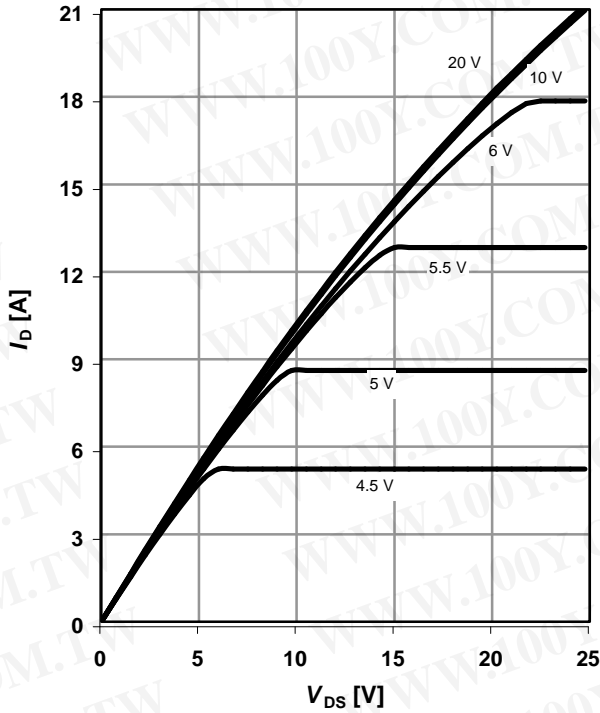
parameter:  $V_{GS}$





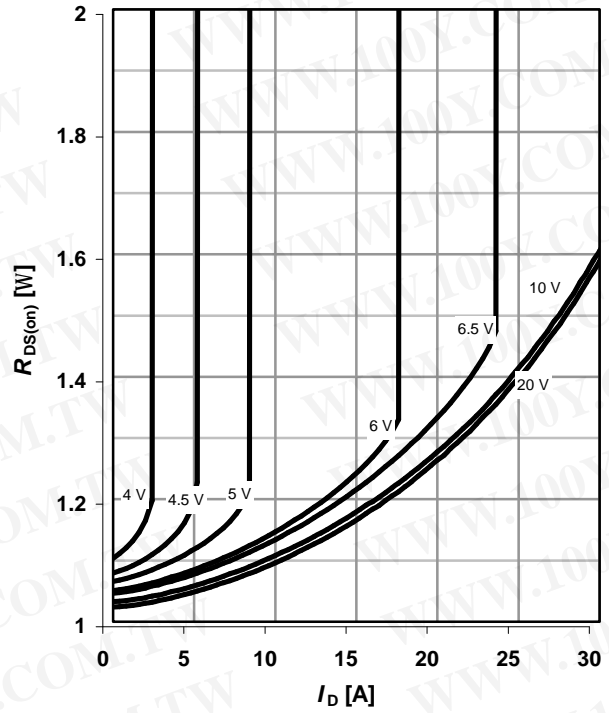
**5 Typ. output characteristics**

$I_D=f(V_{DS}); T_j=150\text{ }^\circ\text{C}; t_p=10\text{ }\mu\text{s}$   
 parameter:  $V_{GS}$



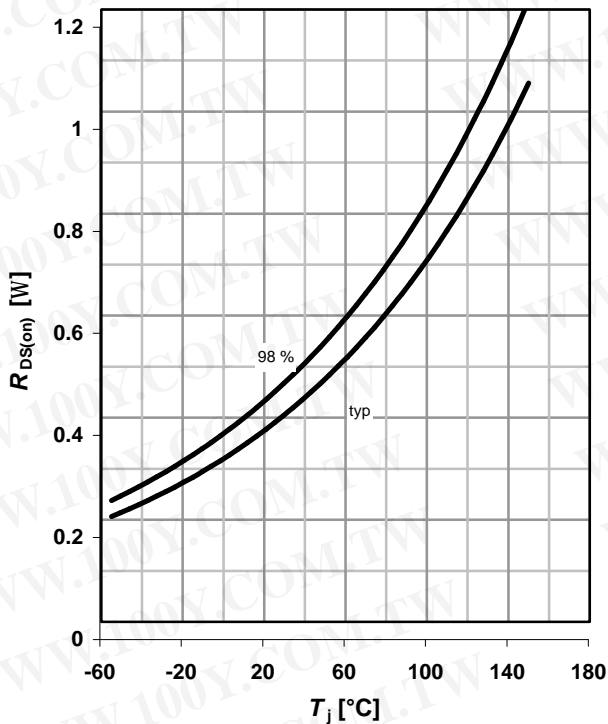
**6 Typ. drain-source on-state resistance**

$R_{DS(on)}=f(I_D); T_j=150\text{ }^\circ\text{C}$   
 parameter:  $V_{GS}$



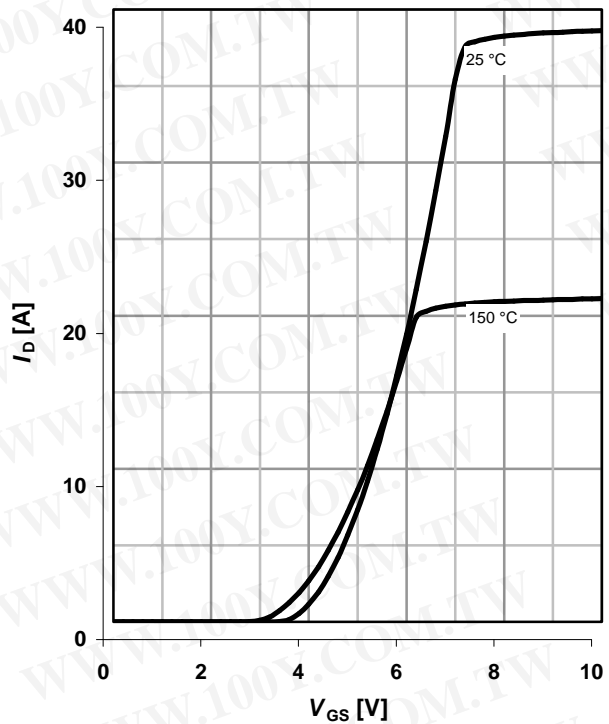
**7 Drain-source on-state resistance**

$R_{DS(on)}=f(T_j); I_D=7.1\text{ A}; V_{GS}=10\text{ V}$



**8 Typ. transfer characteristics**

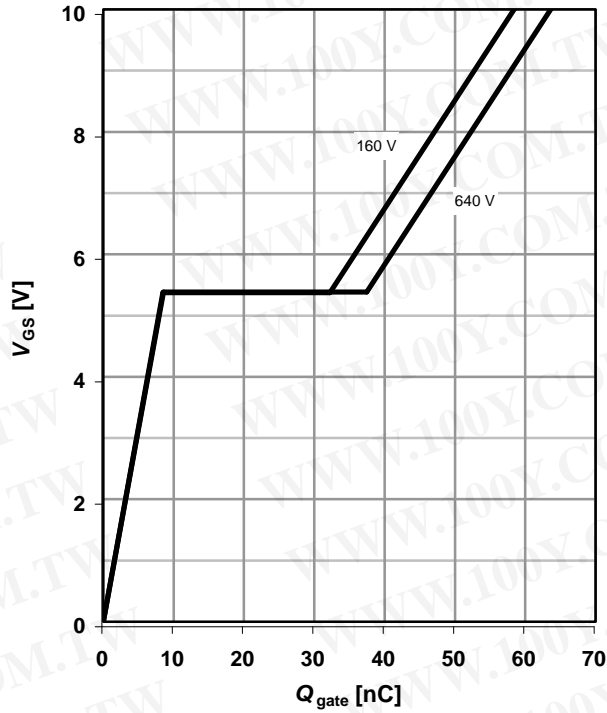
$I_D=f(V_{GS}); |V_{DS}|>2|I_D|R_{DS(on)max}; t_p=10\text{ }\mu\text{s}$   
 parameter:  $T_j$



### 9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=11\text{ A pulsed}$

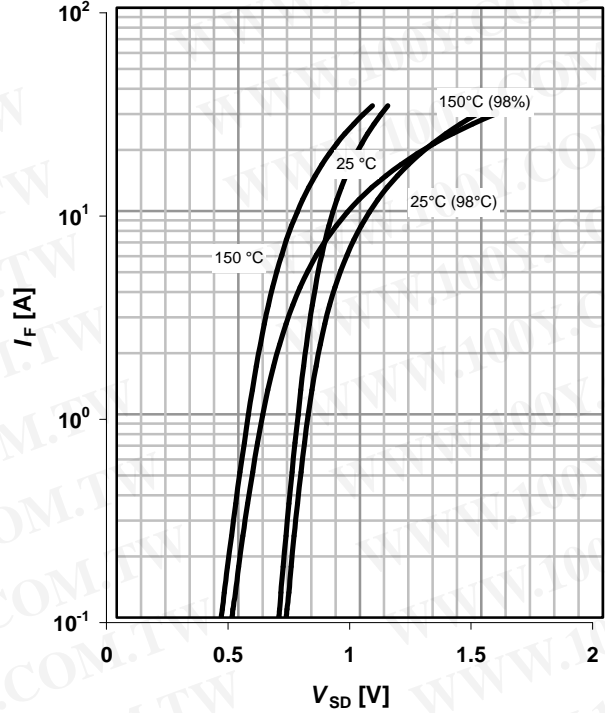
parameter:  $V_{DD}$



### 10 Forward characteristics of reverse diode

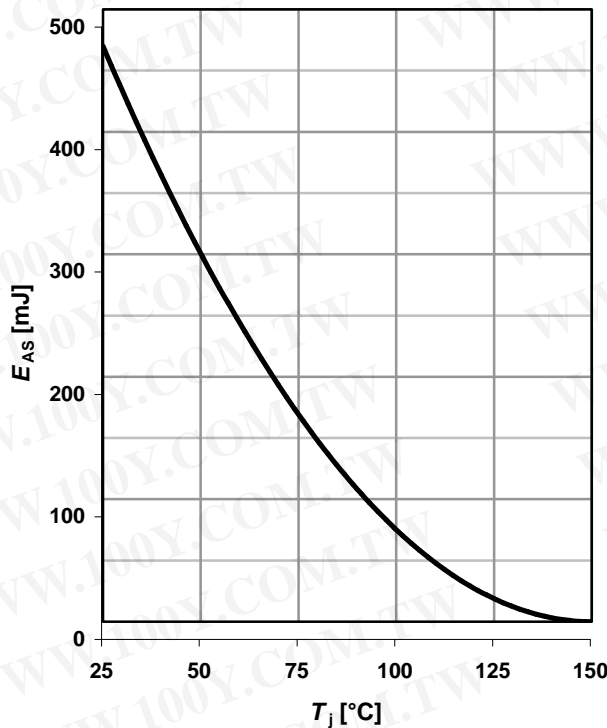
$I_F=f(V_{SD}); t_p=10\ \mu\text{s}$

parameter:  $T_j$



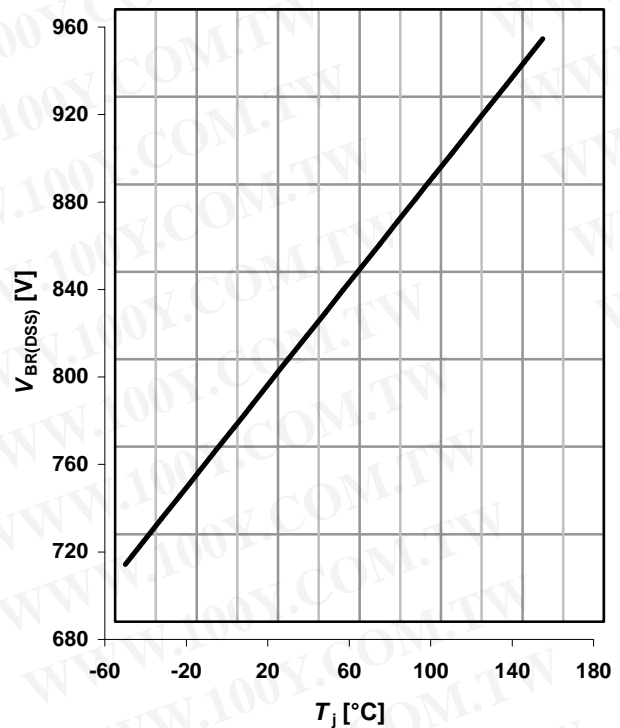
### 11 Avalanche energy

$E_{AS}=f(T_j); I_D=2.2\text{ A}; V_{DD}=50\text{ V}$



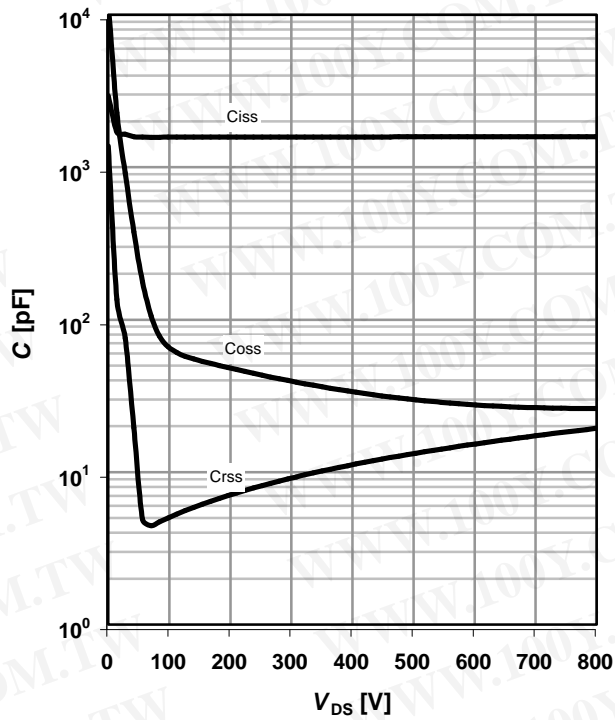
### 12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



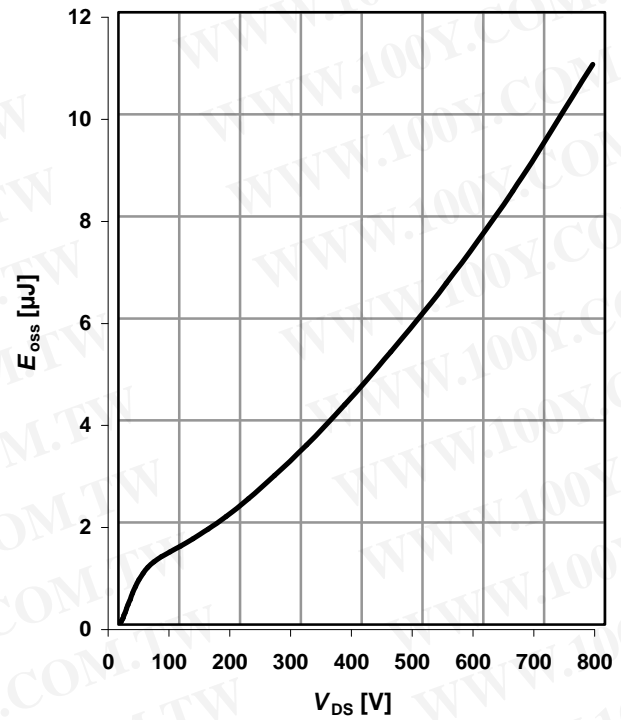
13 Typ. capacitances

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$



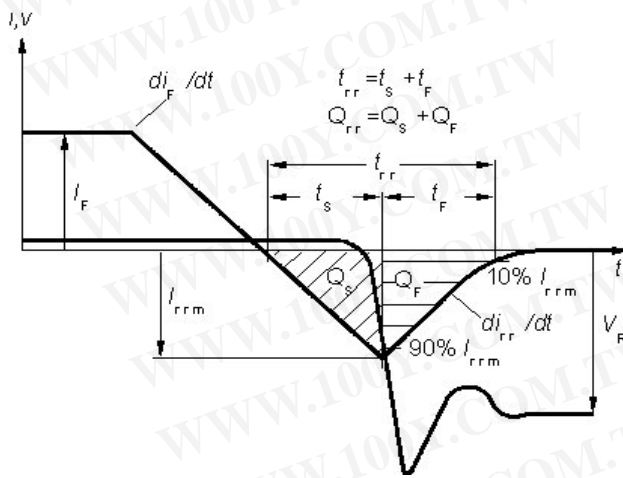
14 Typ. Coss stored energy

$E_{oss}=f(V_{DS})$



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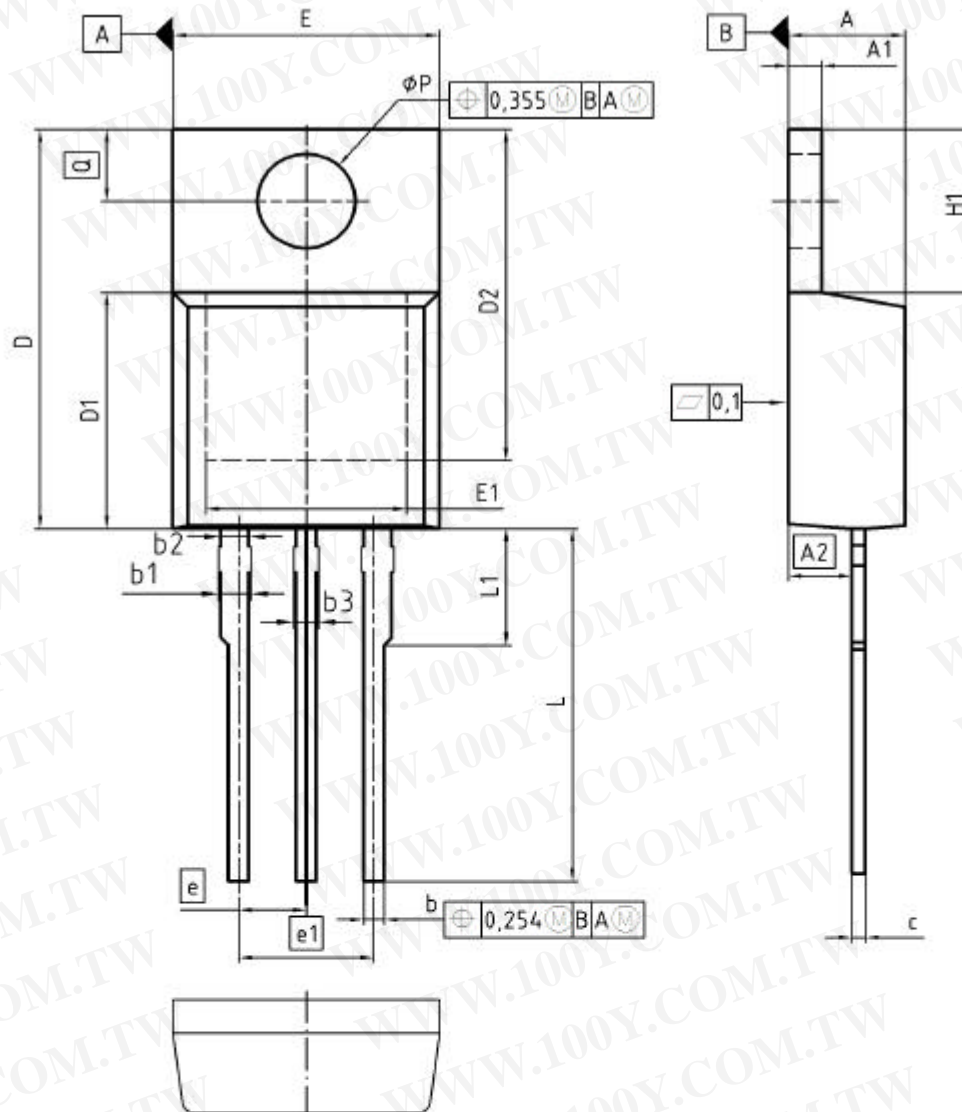
Definition of diode switching characteristics



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PG-TO220-3: Outline



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.57	0.169	0.180
A1	1.17	1.40	0.046	0.055
A2	2.15	2.72	0.085	0.107
b	0.65	0.86	0.026	0.034
b1	0.95	1.40	0.037	0.055
b2	0.95	1.15	0.037	0.045
b3	0.65	1.15	0.026	0.045
c	0.33	0.60	0.013	0.024
D	14.81	15.95	0.583	0.628
D1	8.51	9.45	0.335	0.372
D2	12.19	13.10	0.480	0.516
E	9.70	10.36	0.382	0.408
E1	6.50	8.60	0.256	0.339
e	2.54		0.100	
e1	5.08		0.200	
N	3		3	
H1	5.90	6.90	0.232	0.272
L	13.00	14.00	0.512	0.551
L1	-	4.80	-	0.189
eP	3.60	3.89	0.142	0.153
Q	2.60	3.00	0.102	0.118

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